

Customer No.: 31561  
Docket No.: 11843-US-PA  
Application No.: 10/707,687

**In The Specification:**

1. Please amend the title as "CHIP PACKAGE STRUCTURE WITH HIGH RELIABILITY AND HEAT-DISSIPATING CAPACITY"

2. Please amend paragraphs [0049], [0050] as follows:

[0049] Furthermore, the chipset 250 further comprises a plurality of conductive wires 254b. The carrier 280 has a plurality of contact pads (not shown) thereon. The solder balls 190 are attached to the contact pads on the lower surface of the carrier 280 which is similar or the same to the solder balls 190 shown in Figs 4A~4I. The first active surface 252a of the first chip 250a and the second active surface 252b of the second chip 250b have a plurality of bonding pads (not shown) thereon. The bumps 260 on the second chip 250b are set in the flip-chip bonding gap 256 between the first chip 250a and the second chip 250b. In other words, the second chip 250b is flip-chip bonded to the first active surface 252a of the first chip 250a. Each conductive wire 254b electrically connects a bonding pad on the first chip 250a with a corresponding contact pad on the carrier 280.

[0050] As shown in Fig. 6, an alternative chipset 250 of this embodiment comprises a first chip 250a, a second chip 250b and a third chip 250c. The chipset 250 further includes a plurality of conductive wires 254b. The first chip 250a has a first active surface 252a with a plurality of first bumps 260a thereon. The first chip 250a is bonded and electrically connected to the carrier

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280 in a flip-chip bonding process. The second chip 250b has a second active surface 252b. The second chip 250a is attached to the first chip 250a such that the second active surface 252b face towards a direction away from the first chip 250a. The conductive wires 254b connect the bonding pads on the second active surface 252b of the second chip 250b with corresponding contact pads on the carrier 280. The third chip 250c has a third active surface 252c with a plurality of second bumps 260b thereon. The third chip 250c is bonded and electrically connected to the second chip 250b in a flip-chip bonding process. The first bumps 260a are set in a flip-chip bonding gap between the first chip 250a and the carrier 280 and the second bumps are set in another flip-chip bonding gap 256 between the second chip 250b and the third chip 250c. In other words, the third chip 250c is flip-chip bonded to the second active surface 252b of the second chip 250b and the first chip 250a is flip-chip bonded to the carrier 280. The chip package structure 200 further comprises at least a passive component 195 mounted on the upper surface of the carrier 280 which is similar or the same to passive component 195 shown in Fig. 4H, and the passive component 195 is electrically connected to the carrier 280.